



LDMP- SERIES HIGH POWER PULSED LASER DIODES



LDMP- series of pulsed laser diodes are MQW structure devices with InGaAsP active layers fabricated using advanced MOCVD epitaxial growth techniques. Devices are designed with pulse width FWHM of 50~100ns and repetition frequency up to 15 KHz. Standard TO9mm package with wavelengths of 905, different emitter sizes and stack layers are available for various applications such as range finder and optical measurement.

LDMP-0905

Feature:

- High peak output Power: >50W
- InGaAsP/InGaAsP MQW Structure by MOCVD

Maximum Rating:

Peak Reverse Voltage: V_{rm} 2V

Case Temperature:

Operating -55°C to $+65^{\circ}\text{C}$

Storage -55°C to $+85^{\circ}\text{C}$

Soldering 5 seconds, $+200^{\circ}\text{C}$

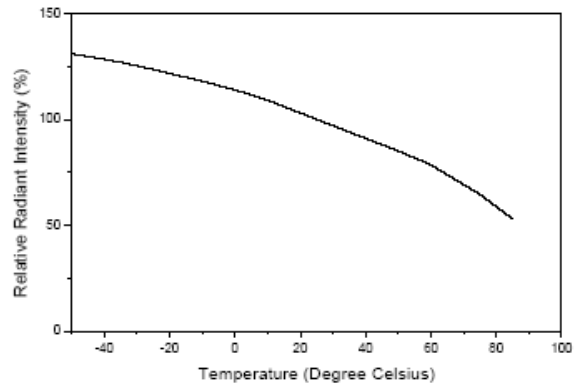
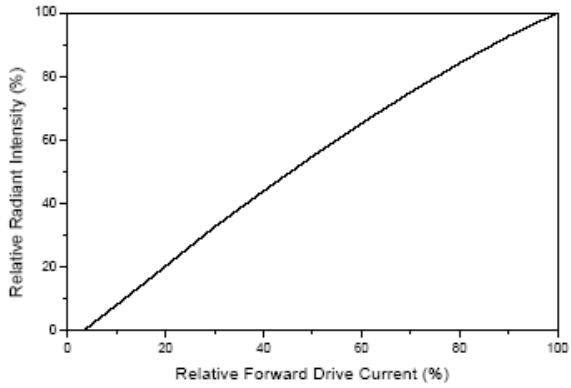


Specifications (25°C):

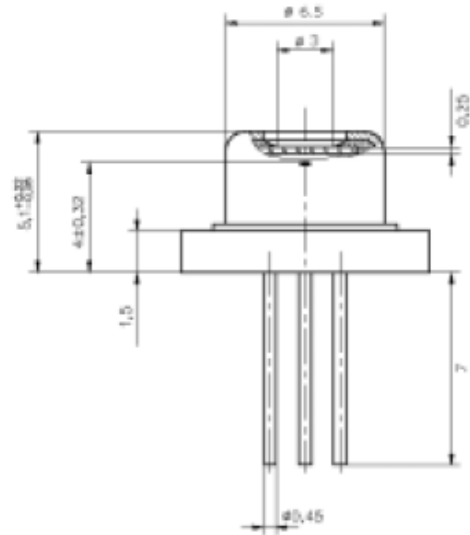
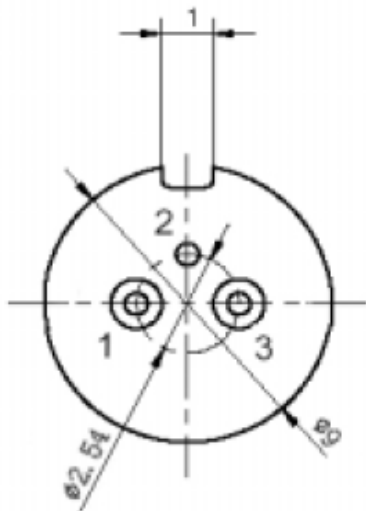
	Symbol	LDMP-0905-20W-51	LDMP-0905-050W-91	LDMP-0905-80W-93	Units
Center Wavelength	λ_0	905	905	905	nm
Wavelength Tolerance		± 10	± 10	± 10	
Peak Forward Current	If	50	50	50	A
Peak Output Power	Po	20	50	70	W
Pulse Width Max.	Tw	50~100	50~100	50~100	ns
Duty Factor	DF	0.05	0.05	0.05	%
Peak Forward Volage	Vf	40	50	52	V
Beam Divergence FWHM	$\theta // \times \theta \perp$	10x40	10x40	10x40	Degree
Source Size	WxH	370x1	400x6	370x200	μm
Number of Laser Diode Element		1	3	3	pcs.
Package		TO-5.6mm with 3 pins	TO-9mm	TO-9mm	



Typical Performance



TO $\Phi 9$ mm Package



1 is LD cathode; 2 is PD anode, 3 is PD cathode